

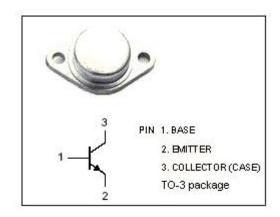
# isc Silicon NPN Power Transistor

### **DESCRIPTION**

- · Collector-Emitter Sustaining Voltage-
  - : V<sub>CEO(SUS)</sub>= 800V(Min)
- · Collector-Emitter Saturation Voltage-
  - :  $V_{CE(sat)}$ = 1.0V(Max)@  $I_C$ = 2A
- · Fast Switching Speed
- Minimum Lot-to-Lot variations for robust device performance and reliable operation

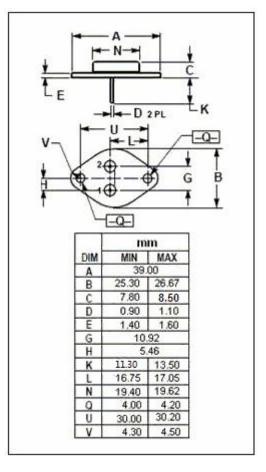


 Designed for high-voltage, high-speed and high power switching applications.



# ABSOLUTE MAXIMUM RATINGS(Ta=25℃)

SYMBOL	PARAMETER	VALUE	UNIT
V <sub>CBO</sub>	Collector-Base Voltage	900	V
V <sub>CEO</sub>	Collector-Emitter Voltage	800	V
V <sub>EBO</sub>	Emitter-Base Voltage	7	V
lc	Collector Current-Continuous	8	Α
I <sub>CM</sub>	Collector Current-Peak	16	Α
Iв	Base Current-Continuous	4	А
Pc	Total Power Dissipation @ Tc=25℃	100	W
TJ	Junction Temperature 150		$^{\circ}$
T <sub>stg</sub>	Storage Temperature Range	-55~150	$^{\circ}$





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2SC2981

#### **ELECTRICAL CHARACTERISTICS**

Tc=25℃ unless otherwise specified

SYMBOL	PARAMETER	CONDITIONS	MIN	MAX	UNIT		
V <sub>CEO(SUS)</sub>	Collector-Emitter Sustaining Voltage	I <sub>C</sub> = 10mA ; R <sub>BE</sub> = ∞	800		V		
V <sub>(BR)EBO</sub>	Emitter-Base Breakdown Voltage	I <sub>E</sub> = 10mA; I <sub>C</sub> = 0	7		V		
V <sub>CE(sat)</sub>	Collector-Emitter Saturation Voltage	I <sub>C</sub> = 2A; I <sub>B</sub> = 0.4A		1.0	V		
V <sub>BE(sat)</sub>	Base-Emitter Saturation Voltage	Ic= 2A; I <sub>B</sub> = 0.4A		1.5	V		
Ісво	Collector Cutoff Current	V <sub>CB</sub> = 850V; I <sub>E</sub> =0		100	μА		
Iceo	Collector Cutoff Current	V <sub>CE</sub> = 650V; R <sub>BE</sub> =0		100	μА		
h <sub>FE-1</sub>	DC Current Gain	I <sub>C</sub> = 0.8A; V <sub>CE</sub> = 5V	15				
h <sub>FE-2</sub>	DC Current Gain	I <sub>C</sub> = 4A; V <sub>CE</sub> = 5V	7				
Switching times							
t <sub>on</sub>	Turn-on Time			1.0	μ \$		
t <sub>stg</sub>	Storage Time	I <sub>C</sub> = 4A, I <sub>B1</sub> = 0.8A; I <sub>B2</sub> = -2A		3.0	μ \$		
t <sub>f</sub>	Fall Time			1.0	μ <b>S</b>		

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